

# PSMNR60-25YLH

N-channel 25 V, 0.7 m $\Omega$ , 300 A logic level MOSFET in LFPAK56 using NextPowerS3 technology

30 September 2019

Product data sheet

### 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package optimized for low  $R_{DSon}$ . Low  $I_{DSS}$  leakage even when hot, high efficiency and high current. Rated to 300 A, optimized for DC load switch and hot-swap applications.

#### 2. Features and benefits

- 100% avalanche tested at I<sub>(AS)</sub> = 190 A
- Optimized for low R<sub>DSon</sub>
- Low leakage < 1 μA at 25 °C</li>
- · Low spiking and ringing for low EMI designs
- · Optimized for 4.5 V gate drive
- · Copper-clip for low parasitic inductance and resistance
- High reliability LFPAK package, qualified to 175 °C
- Wave solderable; exposed leads for optimal solder coverage and visual solder inspection

### 3. Applications

- Hot swap
- e-Fuse
- Power OR-ing
- DC switch / Load switch
- Battery protection
- · Brushed and BLDC (brushless) motor control
- Synchronous rectification in AC-DC and DC-DC applications

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	25	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	300	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	268	W	
Tj	junction temperature			-55	-	175	°C	
Static characte	eristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10		-	0.59	0.7	mΩ	
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10		-	0.82	1.02	mΩ	
Dynamic characteristics								
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V;		2.7	15	30	nC	
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13		19	43	71	nC	



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
S		$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; Fig. 16$		-	1	-	

 <sup>300</sup>A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	ال الله الله الله الله الله الله الله ا	
3	S	source	a	G (F)
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PSMNR60-25YLH	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMNR60-25YLH	H6025L

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	25	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	25	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	268	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	300	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	300	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	1758	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain die	ode					
Is	source current	T <sub>mb</sub> = 25 °C		-	268	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$		-	1758	А
Avalanche rugg	edness					
E <sub>DS(AL)S</sub>		$I_D$ = 25 A; $V_{sup} \le$ 25 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 8.09 ms	[2]	-	3.2	J
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega$	[2]	-	190	А

<sup>[1] 300</sup>A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

<sup>[2]</sup> Protected by 100% test

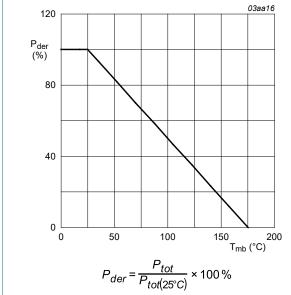
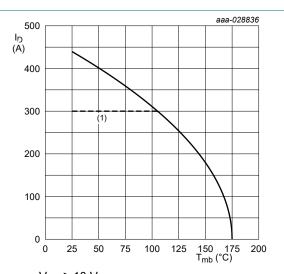
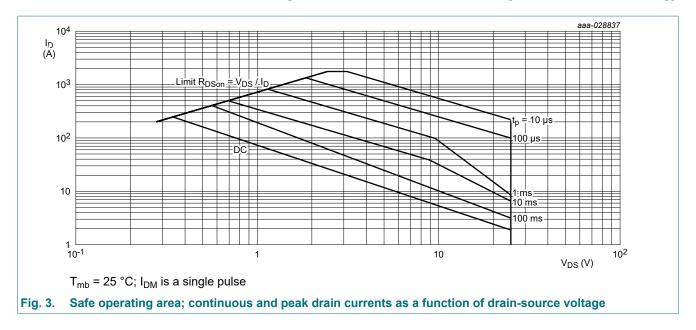


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$  (1) 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

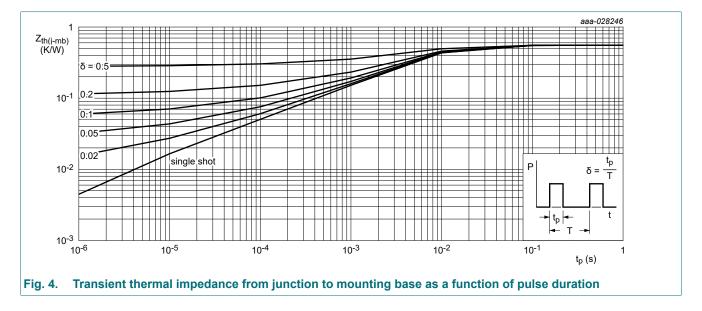
Fig. 2. Continuous drain current as a function of mounting base temperature



### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.48	0.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from	Fig. <u>5</u>	-	42	-	K/W
	junction to ambient	Fig. 6	-	85	-	K/W



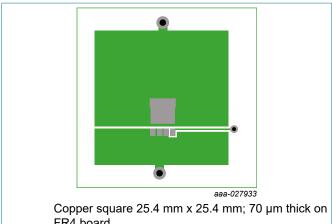
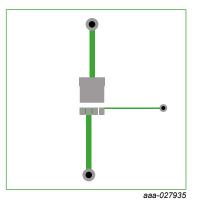


Fig. 5. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

#### 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	25	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	22.5	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}$	1.2	1.64	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-4.7	-	mV/K
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	5.4	-	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	-	0.59	0.7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11	-	-	1.25	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	-	0.82	1.02	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 150 °C; Fig. 11	-	-	1.82	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.56	1.4	3.5	Ω
Dynamic cha	racteristics			'		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	19	43	71	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	40	89	147	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	45	-	nC

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V;		3.2	12	23	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13		2.1	8	15	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			1.1	4.1	7.8	nC
$Q_{GD}$	gate-drain charge			2.7	15	30	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	2.5	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		3247	5411	8117	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>		2047	3412	5118	pF
C <sub>rss</sub>	reverse transfer capacitance			166	616	1478	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 12 V; $R_L$ = 0.4 $\Omega$ ; $V_{GS}$ = 4.5 V;		-	32	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$		-	61	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	50	-	ns
t <sub>f</sub>	fall time			-	44	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	53	-	nC
Source-drai	in diode			'			
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.76	1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	42	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 12 V; <u>Fig. 16</u>	[1]	-	41	-	nC
t <sub>a</sub>	reverse recovery rise time	_		-	21	-	ns
t <sub>b</sub>	reverse recovery fall time			-	21	-	ns
S	softness factor			-	1	-	

#### [1] includes capacitive recovery

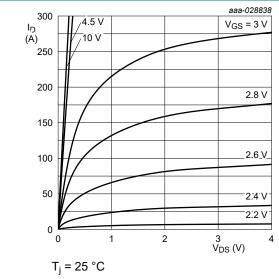


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

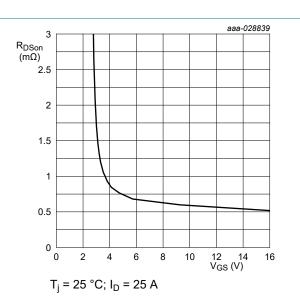


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

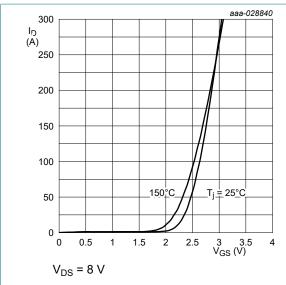


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

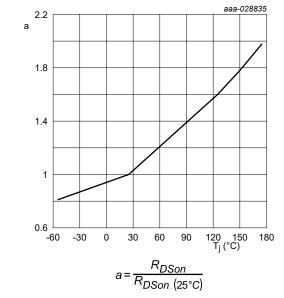


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

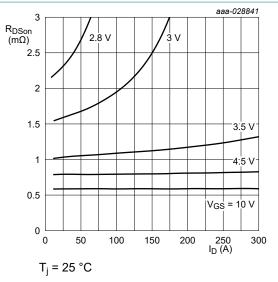


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

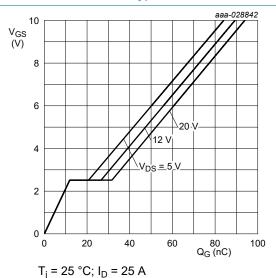


Fig. 12. Gate-source voltage as a function of gate charge; typical values

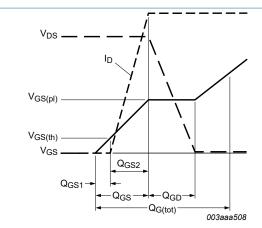
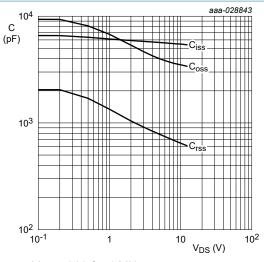


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

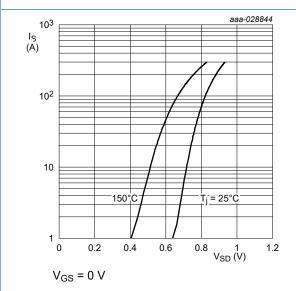


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

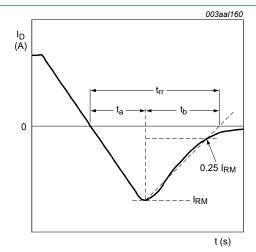
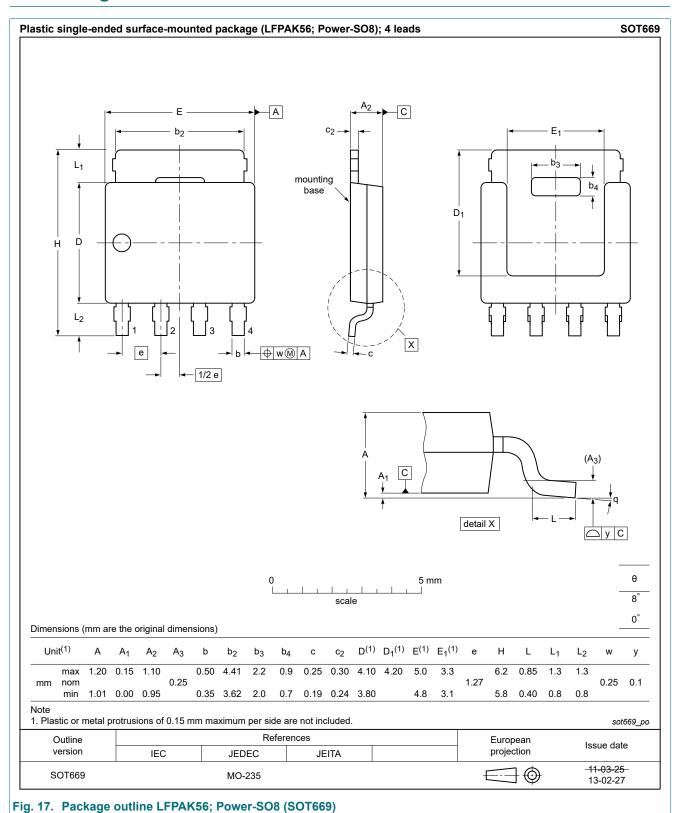
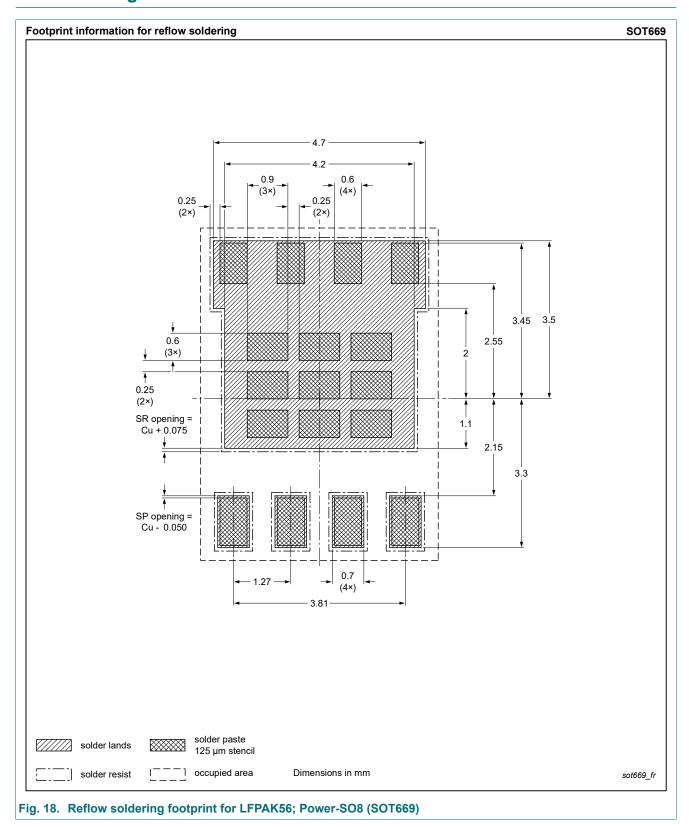


Fig. 16. Reverse recovery timing definition

## 11. Package outline



## 12. Soldering



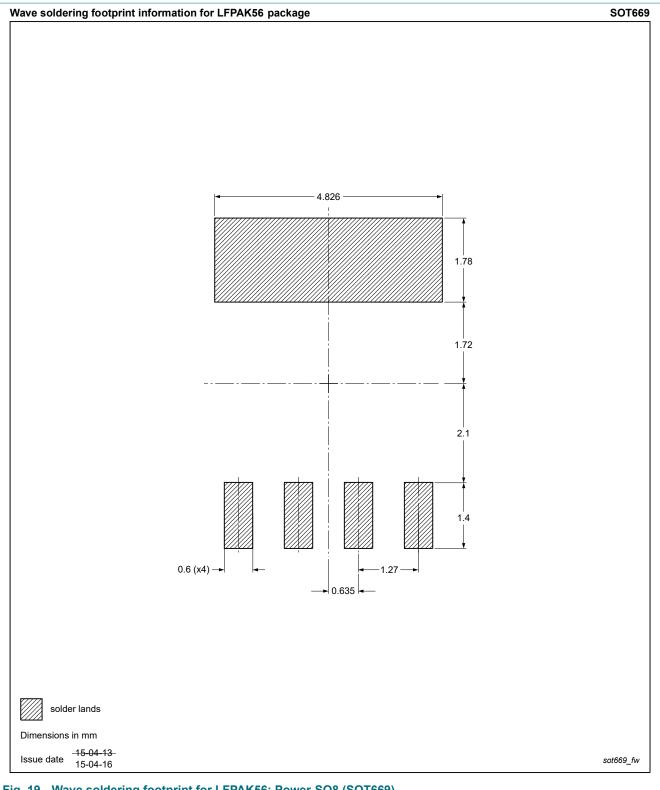


Fig. 19. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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Document status [1][2]	Product status [3]	Definition
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